

LM4810 Boomer[®] Audio Power Amplifier Series

Dual 105mW Headphone Amplifier with Active-High Shutdown Mode

Check for Samples: LM4810

FEATURES

- Active-High Shutdown Mode
- WSON, VSSOP, and SOIC Surface Mount Packaging
- "Click and Pop" Suppression Circuitry
- Low Shutdown Current
- **No Bootstrap Capacitors Required**
- **Unity-Gain Stable**

APPLICATIONS

- **Cellular Phones**
- **Personal Computers**
- **Microphone Preamplifier**
- PDA's

KEY SPECIFICATIONS

- THD+N at 1kHz, 105mW Continuous Average Power into $16\Omega 0.1 \%$ (typ)
- THD+N at 1kHz, 70mW Continuous Average • Power into $32\Omega 0.1 \%$ (typ)
- Shutdown Current 0.4 µA (typ) •

DESCRIPTION

The LM4810 is a dual audio power amplifier capable of delivering 105mW per channel of continuous average power into a 16Ω load with 0.1% (THD+N) from a 5V power supply.

Boomer audio power amplifiers were designed specifically to provide high quality output power with a minimal amount of external components. Since the LM4810 does not require bootstrap capacitors or snubber networks, it is optimally suited for low-power portable systems.

The unity-gain stable LM4810 can be configured by external gain-setting resistors.

The LM4810 features an externally controlled, activehigh, micropower consumption shutdown mode, as well as an internal thermal shutdown protection mechanism.



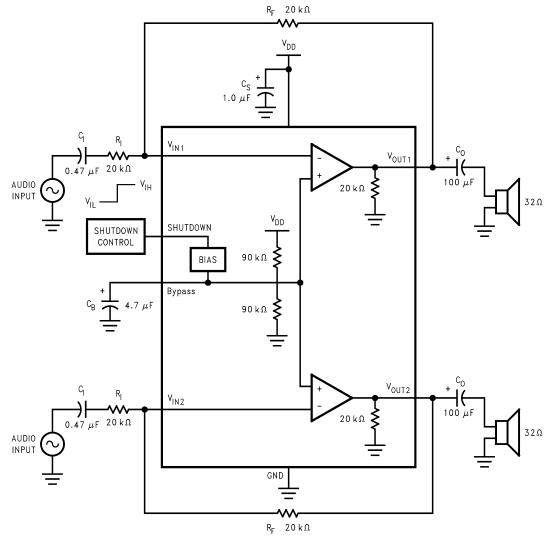
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Typical Application

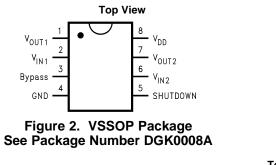


*Refer to Application Information for information concerning proper selection of the input and output coupling capacitors.

Figure 1. Typical Audio Amplifier Application Circuit



Connection Diagrams



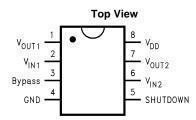
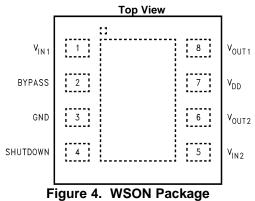


Figure 3. SOIC Package See Package Number D0008A





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RUMENTS



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings ⁽¹⁾⁽²⁾

Supply Voltage	5		6.0V
Storage Temperature			−65°C to +150°C
ESD Susceptibility (3)			3.5kV
ESD Machine Model (4)			250V
Junction Temperature (T _J)	150°C		
Coldering Information		Vapor Phase (60 sec.)	215°C
Soldering Information	SOIC Package	Infrared (15 sec.)	220°C
	θ _{JA} (SOIC)		170°C/W
	θ _{JC} (SOIC)		35°C/W
	θ _{JA} (VSSOP)		210°C/W
Thermal Resistance	θ_{JC} (VSSOP)		56°C/W
	θ _{JA} (WSON)		117°C/W ⁽⁵⁾
	θ _{JA} (WSON)		150°C/W ⁽⁶⁾
	θ _{JC} (WSON)		15°C/W

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

(2) Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

(3) Human body model, 100pF discharged through a $1.5k\Omega$ resistor.

(4) Machine Model ESD test is covered by specification EIAJ IC-121-1981. A 200pF cap is charged to the specified voltage, then discharged directly into the IC with no external series resistor (resistance of discharge path must be under 500hms).

(5) The given θ_{JA} is for an LM4810 packaged in an NGL0008B with the Exposed-Dap soldered to a printed circuit board copper pad with an area equivalent to that of the Exposed-Dap itself.

(6) The given θ_{JA} is for an LM4810 packaged in an NGL0008B with the Exposed-Dap not soldered to any circuit board copper.

Operating Ratings ⁽¹⁾

Temperature Range	$T_{MIN} \le T_A \le T_{MAX}$	−40°C ≤ T _A ≤ 85°C
Supply Voltage (V _{CC}		$2.0V \le V_{CC} \le 5.5V$

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

Electrical Characteristics (1)(2)

The following specifications apply for $V_{DD} = 5V$ unless otherwise specified, limits apply to $T_A = 25^{\circ}C$.

	Barran	Test Osmilitisms	LM	LM4810		
	Parameter	Test Conditions	Тур ⁽³⁾	Limit ⁽⁴⁾	(Limits)	
V _{DD}	Supply Voltage			2.0	V (min)	
				5.5	V (max)	
I _{DD}	Supply Current	$V_{IN} = 0V, I_O = 0A$	1.3	3	mA(max)	
I _{SD}	Shutdown Current	$V_{IN} = 0V, V_{SHUTDOWN} = V_{DD}$	0.4	2	µA(max)	
V _{OS}	Output Offset Voltage	$V_{IN} = 0V$	4.0	50	mV(max)	
Po	Output Power	THD+N = 0.1%, f = 1kHz				
		$R_L = 16\Omega$	105		mW	
		$R_L = 32\Omega$	70	65	mW(min)	
THD+N	Total Harmonic Distortion	$P_O = 50$ mW, $R_L = 32\Omega$ f = 20Hz to 20kHz	0.3		%	
Crosstalk	Channel Separation	$R_{L} = 32\Omega; P_{O} = 70mW$	70		dB	

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

(2) All voltages are measured with respect to the ground pin, unless otherwise specified.

(3) Typical specifications are specified at +25OC and represent the most likely parametric norm.

(4) Datasheet max/min specification limits are ensured by design, test, or statistical analysis.

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Electrical Characteristics ⁽¹⁾⁽²⁾ (continued)

The following specifications apply for $V_{DD} = 5V$ unless otherwise specified, limits apply to $T_A = 25^{\circ}C$.

	Donom of or	Test Canditions	LM	LM4810		
Parameter		Test Conditions	Тур ⁽³⁾	Limit ⁽⁴⁾	(Limits)	
PSRR	Power Supply Rejection Ratio	$C_B = 1.0 \mu F$; $V_{RIPPLE} = 200 m V_{PP}$, f = 1kHz; Input terminated into 50Ω	70		dB	
V _{SDIH}	Shutdown Voltage Input High			0.8 x V _{DD}	V (min)	
V _{SDIL}	Shutdown Voltage Input Low			0.2 x V _{DD}	V (max)	

Electrical Characteristics ⁽¹⁾⁽²⁾

The following specifications apply for V_{DD} = 3.3V unless otherwise specified, limits apply to T_A = 25°C.

Parameter		Test Oser litizer	LM	Units		
	Parameter	Test Conditions	Тур ⁽³⁾	Limit ⁽⁴⁾	(Limits)	
I _{DD}	Supply Current	$V_{IN} = 0V, I_O = 0A$	1.0		mA	
I _{SD}	Shutdown Current	$V_{IN} = 0V, V_{SHUTDOWN} = V_{DD}$	0.4		μA	
V _{OS}	Output Offset Voltage	$V_{IN} = 0V$	4.0		mV	
P _O Output Power		THD+N = 0.1%, f = 1kHz				
		$R_L = 16\Omega$	40		mW	
		$R_L = 32\Omega$	28		mW	
THD+N Total Harmonic Distortion		$P_O = 25$ mW, $R_L = 32\Omega$ f = 20Hz to 20kHz	0.4		%	
Crosstalk	Channel Separation	$R_{L} = 32\Omega; P_{O} = 25mW$	70		dB	
PSRR Power Supply Rejection Ratio		$C_B = 1.0\mu$ F; Vripple = 200mV _{PP} , f = 1kHz; Input terminated into 50 Ω	70		dB	
V _{SDIH}	Shutdown Voltage Input High			0.8 x V _{DD}	V (min)	
V _{SDIL}	Shutdown Voltage Input Low			0.2 x V _{DD}	V (max)	

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

(2) All voltages are measured with respect to the ground pin, unless otherwise specified.

(3) Typical specifications are specified at +25OC and represent the most likely parametric norm.

(4) Datasheet max/min specification limits are ensured by design, test, or statistical analysis.

Electrical Characteristics ⁽¹⁾⁽²⁾

The following specifications apply for V_{DD} = 2.6V unless otherwise specified, limits apply to T_A = 25°C.

	Demonster	Test Ose ditions	LM	Units		
	Parameter	Test Conditions	Тур ⁽³⁾	Limit ⁽⁴⁾	(Limits)	
I _{DD}	Supply Current	$V_{IN} = 0V, I_O = 0A$	0.9		mA	
I _{SD}	Shutdown Current	$V_{IN} = 0V, V_{SHUTDOWN} = V_{DD}$	0.2		μA	
V _{OS}	Output Offset Voltage	$V_{IN} = 0V$	4.0		mV	
Po	Output Power	THD+N = 0.1%, f = 1kHz				
		$R_L = 16\Omega$	20		mW	
		$R_L = 32\Omega$	16		mW	
THD+N	Total Harmonic Distortion	$P_O = 15$ mW, $R_L = 32\Omega$ f = 20Hz to 20kHz	0.6		%	
Crosstalk	Channel Separation	$R_{L} = 32\Omega; P_{O} = 15mW$	70		dB	
PSRR	Power Supply Rejection Ratio	$C_B = 1.0\mu$ F; Vripple = 200mV _{PP} , f = 1kHz; Input terminated into 50 Ω	70		dB	
V _{SDIH}	Shutdown Voltage Input High			0.8 x V _{DD}	V (min)	
V _{SDIL}	Shutdown Voltage Input Low			0.2 x V _{DD}	V (max)	

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

(2) All voltages are measured with respect to the ground pin, unless otherwise specified.

(3) Typical specifications are specified at +25OC and represent the most likely parametric norm.

(4) Datasheet max/min specification limits are ensured by design, test, or statistical analysis.

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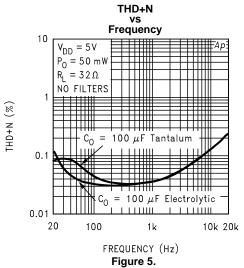
External Components Description

Components	Functional Description (See Figure 1)						
1. R _i	The inverting input resistance, along with R_f , set the closed-loop gain. R_i , along with C_i , form a high pass filter with $f_c = 1/(2\pi R_i C_i)$.						
2. C_i The input coupling capacitor blocks DC voltage at the amplifier's input terminals. C_i , along with R_i , create a highpass filter with $f_c = 1/(2\pi R_i C_i)$. Refer to SELECTING PROPER EXTERNAL COMPONENTS, for an explanation of determining the value of C_i .							
3. R _f	The feedback resistance, along with R _i , set closed-loop gain.						
4. C _S	This is the supply bypass capacitor. It provides power supply filtering. Refer to Application Information for proper placement and selection of the supply bypass capacitor.						
5. C _B	This is the BYPASS pin capacitor. It provides half-supply filtering. Refer to SELECTING PROPER EXTERNAL COMPONENTS for information concerning proper placement and selection of C _B .						
6. C _O	This is the output coupling capacitor. It blocks the DC voltage at the amplifier's output and forms a high pass filter with R_L at $f_O = 1/(2\pi R_L C_O)$						

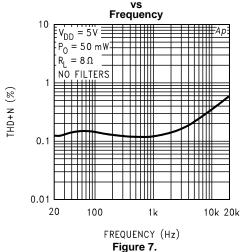




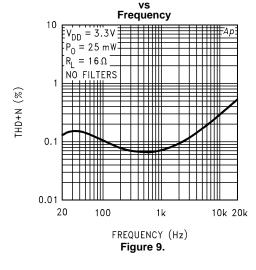
Typical Performance Characteristics











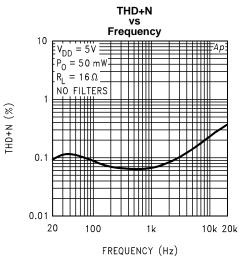
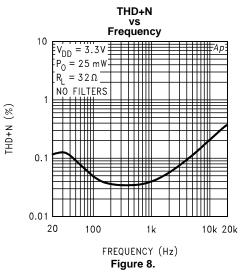
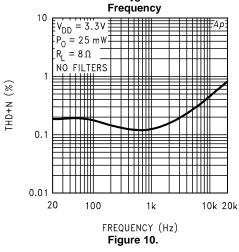


Figure 6.



THD+N vs



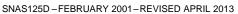
THD+N (%)

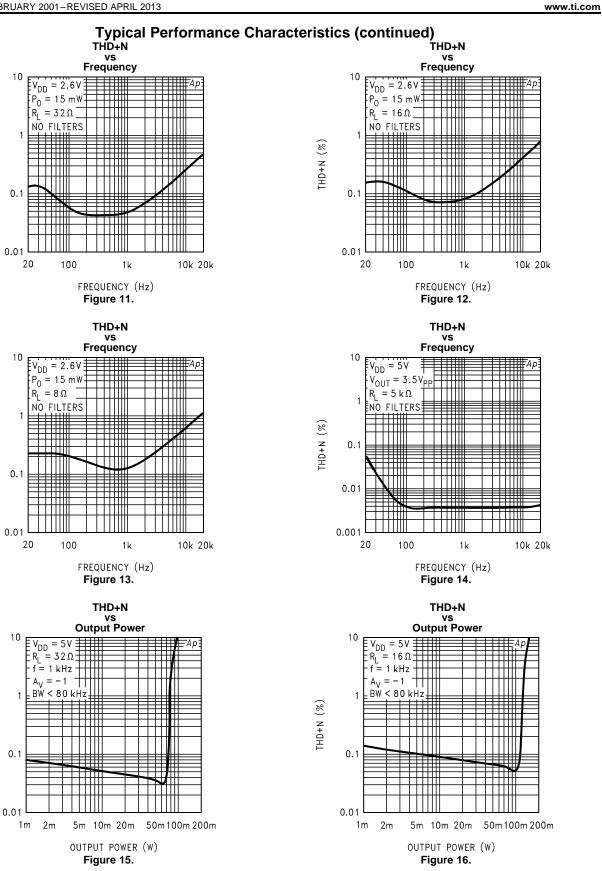
THD+N (%)

THD+N (%)

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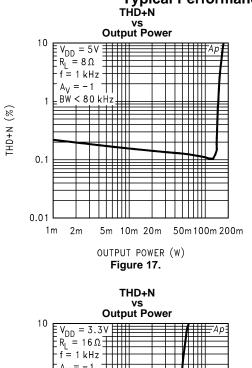
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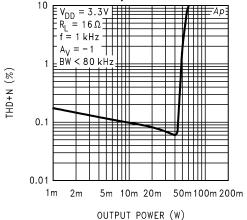
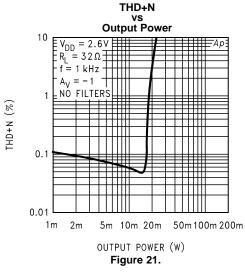
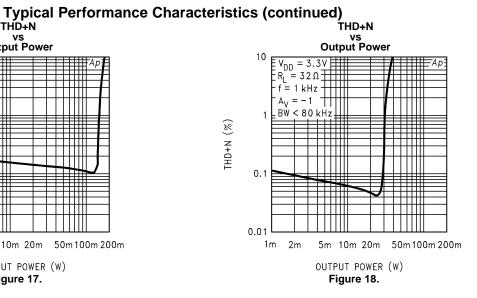


Figure 19.





THD+N

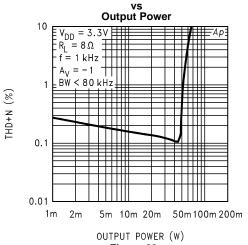
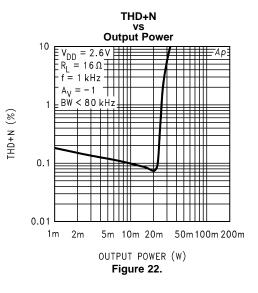
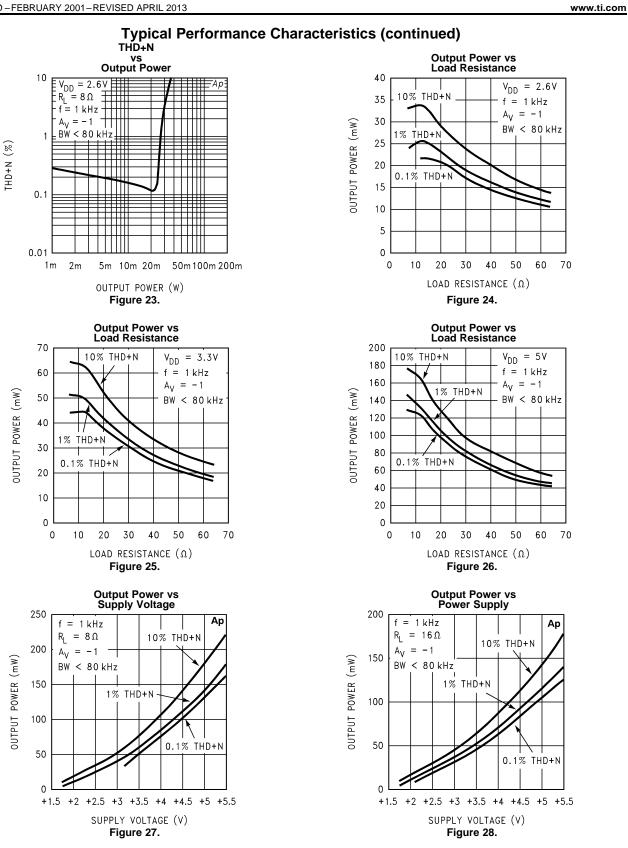


Figure 20.



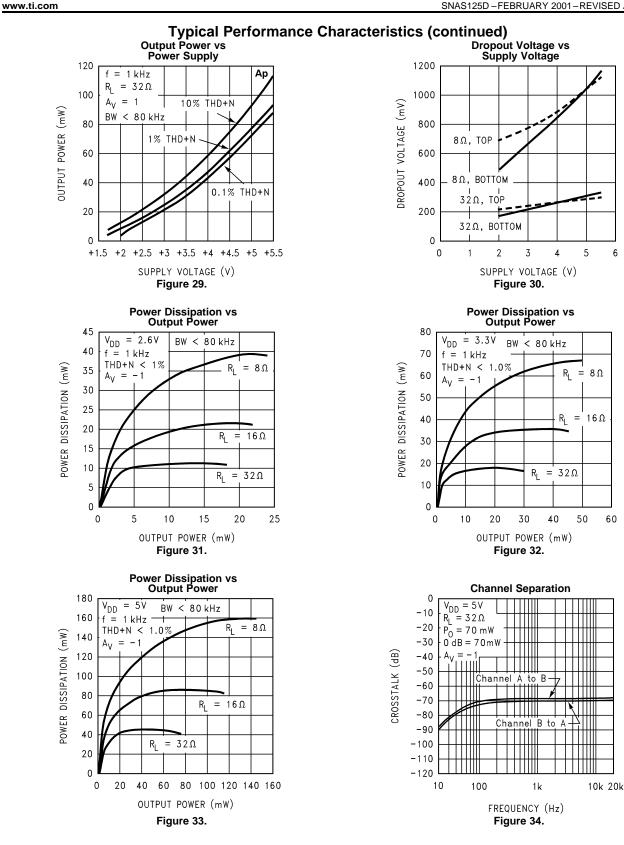
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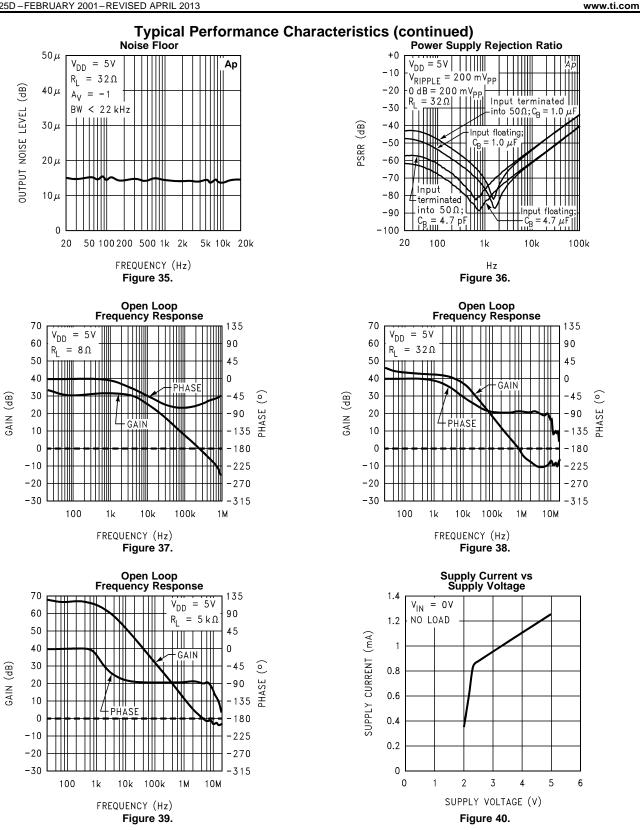
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APPLICATION INFORMATION

MICRO-POWER SHUTDOWN

The voltage applied to the SHUTDOWN pin controls the LM4810's shutdown function. Activate micro-power shutdown by applying a logic high voltage to the SHUTDOWN pin. The logic threshold is typically $V_{DD}/2$. When active, the LM4810's micro-power shutdown feature turns off the amplifier's bias circuitry, reducing the supply current. The low 0.4µA typical shutdown current is achieved by applying a voltage that is as near as V_{DD} as possible to the SHUTDOWN pin. A voltage that is less than V_{DD} may increase the shutdown current.

There are a few ways to control the micro-power shutdown. These include using a single-pole, single-throw switch, a microprocessor, or a microcontroller. When using a switch, connect an external 100k Ω pull-up resistor between the SHUTDOWN pin and V_{DD}. Connect the switch between the SHUTDOWN pin and GND. Select normal amplifier operation by closing the switch. Opening the switch connects the SHUTDOWN pin to V_{DD} through the pull-up resistor, activating micro-power shutdown. The switch and resistor ensure that the SHUTDOWN pin will not float. This prevents unwanted state changes. In a system with a microprocessor or a microcontroller, use a digital output to apply the control voltage to the SHUTDOWN pin. Driving the SHUTDOWN pin with active circuitry eliminates the pull-up resistor.

EXPOSED-DAP PACKAGE PCB MOUNTING CONSIDERATION

The LM4810's exposed-Dap (die attach paddle) package (NGL0008B) provides a low thermal resistance between the die and the PCB to which the part is mounted and soldered. This allows rapid heat transfer from the die to the surrounding PCB copper traces, ground plane, and surrounding air.

The NGL0008B package should have its DAP soldered to a copper pad on the PCB. The DAP's PCB copper pad may be connected to a large plane of continuous unbroken copper. This plane forms a thermal mass, heat sink, and radiation area.

However, since the LM4810 is designed for headphone applications, connecting a copper plane to the DAP's PCB copper pad is not required. Figure 33 in Typical Performance Characteristics shows that the maximum power dissipated is just 45mW per amplifier with a 5V power supply and a 32Ω load.

Further detailed and specific information concerning PCB layout, fabrication, and mounting an NGL0008B (WSON) package is available from Texas Instruments' Package Engineering Group under application note AN1187.

POWER DISSIPATION

Power dissipation is a major concern when using any power amplifier and must be thoroughly understood to ensure a successful design. Equation 1 states the maximum power dissipation point for a single-ended amplifier operating at a given supply voltage and driving a specified output load.

$$P_{DMAX} = (V_{DD})^2 / (2\pi^2 R_L)$$

(1)

Since the LM4810 has two operational amplifiers in one package, the maximum internal power dissipation point is twice that of the number which results from Equation 1. Even with the large internal power dissipation, the LM4810 does not require heat sinking over a large range of ambient temperature. From Equation 1, assuming a 5V power supply and a 32Ω load, the maximum power dissipation point is 40mW per amplifier. Thus the maximum package dissipation point is 80mW. The maximum power dissipation point obtained must not be greater than the power dissipation that results from Equation 2:

$$\mathsf{P}_{\mathsf{DMAX}} = (\mathsf{T}_{\mathsf{JMAX}} - \mathsf{T}_{\mathsf{A}}) / \theta_{\mathsf{JA}}$$

(2)

For package DGK0008A, $\theta_{JA} = 210^{\circ}$ C/W. $T_{JMAX} = 150^{\circ}$ C for the LM4810. Depending on the ambient temperature, T_A , of the system surroundings, Equation 2 can be used to find the maximum internal power dissipation supported by the IC packaging. If the result of Equation 1 is greater than that of Equation 2, then either the supply voltage must be decreased, the load impedance increased or T_A reduced. For the typical application of a 5V power supply, with a 32 Ω load, the maximum ambient temperature possible without violating the maximum junction temperature is approximately 133.2°C provided that device operation is around the maximum power dissipation point. Power dissipation is a function of output power and thus, if typical operation is not around the maximum power dissipation point, the ambient temperature may be increased accordingly. Refer to Typical Performance Characteristics for power dissipation information for lower output powers.

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POWER SUPPLY BYPASSING

As with any power amplifier, proper supply bypassing is critical for low noise performance and high power supply rejection. Applications that employ a 5V regulator typically use a 10μ F in parallel with a 0.1μ F filter capacitors to stabilize the regulator's output, reduce noise on the supply line, and improve the supply's transient response. However, their presence does not eliminate the need for a local 1.0μ F tantalum bypass capacitance connected between the LM4810's supply pins and ground. Keep the length of leads and traces that connect capacitor, C_B, between the BYPASS pin and ground improves the internal bias voltage's stability and improves the amplifier's PSRR. The PSRR improvements increase as the bypass pin capacitor value increases. Too large, however, increases the amplifier's turn-on time. The selection of bypass capacitor values, especially C_B, depends on desired PSRR requirements, click and pop performance (as explained in SELECTING PROPER EXTERNAL COMPONENTS), system cost, and size constraints.

SELECTING PROPER EXTERNAL COMPONENTS

Optimizing the LM4810's performance requires properly selecting external components. Though the LM4810 operates well when using external components with wide tolerances, best performance is achieved by optimizing component values.

The LM4810 is unity-gain stable, giving a designer maximum design flexibility. The gain should be set to no more than a given application requires. This allows the amplifier to achieve minimum THD+N and maximum signal-to-noise ratio. These parameters are compromised as the closed-loop gain increases. However, low gain demands input signals with greater voltage swings to achieve maximum output power. Fortunately, many signal sources such as audio CODECs have outputs of $1V_{RMS}$ (2.83V_{P-P}). Please refer to AUDIO POWER AMPLIFIER DESIGN for more information on selecting the proper gain.

Input and Output Capacitor Value Selection

Amplifying the lowest audio frequencies requires high value input and output coupling capacitors (C_1 and C_0 in Figure 1). A high value capacitor can be expensive and may compromise space efficiency in portable designs. In many cases, however, the speakers used in portable systems, whether internal or external, have little ability to reproduce signals below 150Hz. Applications using speakers with this limited frequency response reap little improvement by using high value input and output capacitors.

Besides affecting system cost and size, C_i has an effect on the LM4810's click and pop performance. The magnitude of the pop is directly proportional to the input capacitor's size. Thus, pops can be minimized by selecting an input capacitor value that is no higher than necessary to meet the desired -3dB frequency. Please refer to the OPTIMIZING CLICK AND POP REDUCTION PERFORMANCE for a more detailed discussion on click and pop performance.

As shown in Figure 1, the input resistor, R_I and the input capacitor, C_I , produce a -3dB high pass filter cutoff frequency that is found using Equation 3. In addition, the output load R_L , and the output capacitor C_O , produce a -3db high pass filter cutoff frequency defined by Equation 4.

$f_{I-3db}=1/2\pi R_I C_I$		(3)
$f_{O-3db}=1/2\pi R_L C_O$		(4)

Also, careful consideration must be taken in selecting a certain type of capacitor to be used in the system. Different types of capacitors (tantalum, electrolytic, ceramic) have unique performance characteristics and may affect overall system performance.

Bypass Capacitor Value Selection

Besides minimizing the input capacitor size, careful consideration should be paid to the value of C_B , the capacitor connected to the BYPASS pin. Since C_B determines how fast the LM4810 settles to quiescent operation, its value is critical when minimizing turn-on pops. The slower the LM4810's outputs ramp to their quiescent DC voltage (nominally 1/2 V_{DD}), the smaller the turn-on pop. Choosing C_B equal to 4.7µF along with a small value of C_i (in the range of 0.1µF to 0.47µF), produces a click-less and pop-less shutdown function. As discussed above, choosing C_i no larger than necessary for the desired bandwith helps minimize clicks and pops.



OPTIMIZING CLICK AND POP REDUCTION PERFORMANCE

The LM4810 contains circuitry that minimizes turn-on and shutdown transients or "clicks and pop". For this discussion, turn-on refers to either applying the power supply voltage or when the shutdown mode is deactivated. During turn-on, the LM4810's internal amplifiers are configured as unity gain buffers. An internal current source charges up the capacitor on the BYPASS pin in a controlled, linear manner. The gain of the internal amplifiers remains unity until the voltage on the BYPASS pin reaches $1/2 V_{DD}$. As soon as the voltage on the BYPASS pin is stable, the device becomes fully operational. During device turn-on, a transient (pop) is created from a voltage difference between the input and output of the amplifier as the voltage on the BYPASS pin reaches $1/2 V_{DD}$. For this discussion, the input of the amplifier refers to the node between R₁ and C₁. Ideally, the input and output track the voltage applied to the BYPASS pin. During turn-on, the buffer-configured amplifier output charges the input capacitor, C₁, through the input resistor, R₁. This input resistor delays the charging time of C₁ thereby causing the voltage difference between the input and output that results in a transient (pop). Higher value capacitors need more time to reach a quiescent DC voltage (usually $1/2 V_{DD}$) when charged with a fixed current. Decreasing the value of C₁ and R₁ will minimize the turn-on pops at the expense of the desired -3dB frequency.

Although the BYPASS pin current cannot be modified, changing the size of C_B alters the device's turn-on time and the magnitude of "clicks and pops". Increasing the value of C_B reduces the magnitude of turn-on pops. However, this presents a tradeoff: as the size of C_B increases, the turn-on time increases. There is a linear relationship between the size of C_B and the turn-on time. Here are some typical turn-on times for various values of C_B :

Св	T _{ON}
0.1µF	80ms
0.22µF	170ms
0.33µF	270ms
0.47µF	370ms
0.68µF	490ms
1.0µF	920ms
2.2µF	1.8sec
3.3µF	2.8sec
4.7µF	3.4sec
10µF	7.7sec

In order eliminate "clicks and pops", all capacitors must be discharged before turn-on. Rapidly switching V_{DD} may not allow the capacitors to fully discharge, which may cause "clicks and pops". In a single-ended configuration, the output is coupled to the load by C_0 . This capacitor usually has a high value. C_0 discharges through internal 20k Ω resistors. Depending on the size of C_0 , the discharge time constant can be relatively large. To reduce transients in single-ended mode, an external $1k\Omega$ –5k Ω resistor can be placed in parallel with the internal 20k Ω resistor. The tradeoff for using this resistor is increased quiescent current.

AUDIO POWER AMPLIFIER DESIGN

Design a Dual 70mW/32Ω Audio Amplifier

Given:	
Power Output	70 mW
Load Impedance	32Ω
Input Level	1 Vrms (max)
Input Impedance	20kΩ
Bandwidth	100 Hz–20 kHz ± 0.50dB

The design begins by specifying the minimum supply voltage necessary to obtain the specified output power. One way to find the minimum supply voltage is to use Figure 27 in Typical Performance Characteristics. Another way, using Equation 5, is to calculate the peak output voltage necessary to achieve the desired output power for a given load impedance. To account for the amplifier's dropout voltage, two additional voltages, based on Figure 30 in Typical Performance Characteristics, must be added to the result obtained by Equation 5. For a single-ended application, the result is Equation 6.

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 $V_{DD} \ge (2V_{OPEAK} + (V_{ODTOP} + V_{ODBOT}))$

 $V_{\text{opeak}} = \sqrt{(2R_1P_0)}$

gain variation for both response limits is 0.17dB, well within the
$$\pm 0.25$$
dB desired limit. The results are an $f_L = 100$ Hz/5 = 20Hz (9)

and a

bandwidth limit

As stated in External Components Description, both R_i in conjunction with C_i, and C_o with R_L, create first order highpass filters. Thus to obtain the desired low frequency response of 100Hz within ±0.5dB, both poles must be taken into consideration. The combination of two single order filters at the same frequency forms a second order response. This results in a signal which is down 0.34dB at five times away from the single order filter -3dB point. Thus, a frequency of 20Hz is used in the following equations to ensure that the response is better than 0.5dB down at 100Hz.

$$C_i ≥ 1 / (2π * 20kΩ * 20Hz) = 0.397μF; use 0.39μF.$$

$$C_o ≥ 1 / (2π * 32Ω * 20Hz) = 249μF; use 330μF.$$
(11)
(12)

he high frequency pole is determined by the product of the desired high frequency pole,
$$f_H$$
, and f_H , h_H and f_H and f_H and f_H are coulting CPWP = 150kHz which

Th nd the closed-loop gain, A_V . With a closed-loop gain of 1.5 and $f_H = 100$ kHz, the resulting GBWP = 150kHz which is much smaller than the LM4810's GBWP of 900kHz. This figure displays that if a designer has a need to design an amplifier with a higher gain, the LM4810 can still be used without running into bandwidth limitations.

$$A_{V} \geq \sqrt{(P_{0}R_{L})}/(V_{IN}) = V_{orms}/V_{inrms}$$
⁽⁷⁾

Thus, a minimum gain of 1.497 allows the LM4810 to reach full output swing and maintain low noise and THD+N performance. For this example, let
$$A_V$$
=1.5.

The amplifiers overall gain is set using the input (
$$R_i$$
) and feedback (R_f) resistors. With the desired input impedance set at 20k Ω , the feedback resistor is found using Equation 8.

$$A_V = R_f/R_i$$

The value of R_f is 30k Ω .

$$f_{L} = 100HZ/5 = 20HZ$$

a
 $f_{H} = 20kHz^{*}5 = 100kHz$

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(5) (6)

(8)

(10)



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Demonstration Board Schematic

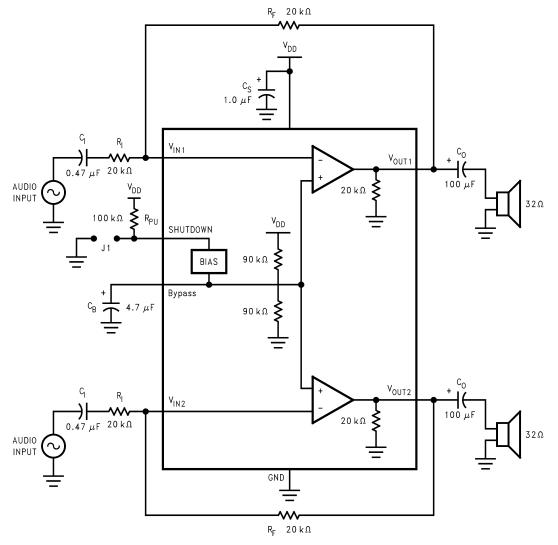
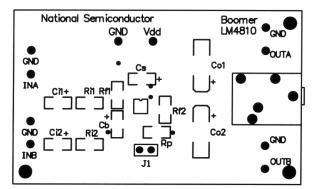


Figure 41. LM4810 Demonstration Board Schematic

Demonstration Board Layout







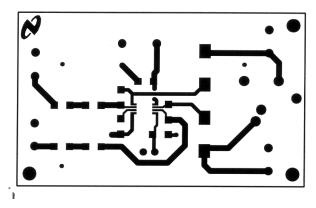


Figure 43. Recommended PC Board Layout Component-Side Layout

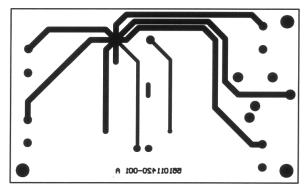


Figure 44. Recommended PC Board Layout Bottom-Side Layout

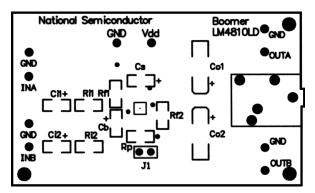


Figure 45. Recommended NGL0008B PC Board Layout Component-Side Silkreen



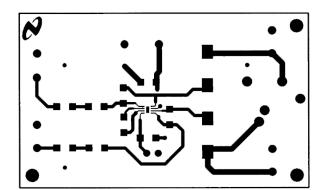


Figure 46. Recommended NGL0008B PC Board Layout Component-Side Layout

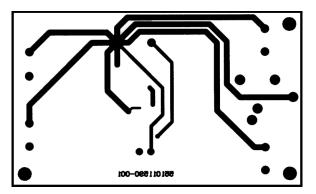


Figure 47. Recommended NGL0008B PC Board Layout Bottom-Side Layout

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Ch	nanges from Revision C (April 2013) to Revision D	Page
•	Changed layout of National Data Sheet to TI format	. 19

Texas

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
LM4810MM/NOPB	ACTIVE	VSSOP	DGK	8	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	G10	Samples
LM4810MMX/NOPB	ACTIVE	VSSOP	DGK	8	3500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 85	G10	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM4810MM/NOPB	VSSOP	DGK	8	1000	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM4810MMX/NOPB	VSSOP	DGK	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM4810MM/NOPB	VSSOP	DGK	8	1000	210.0	185.0	35.0
LM4810MMX/NOPB	VSSOP	DGK	8	3500	367.0	367.0	35.0

DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.

- D Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



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